

SVC202, 202SPA

Duffused Junction Type Silicon Diode Varactor Diode (IOCAP) for FM Receiver Electronic Tuning

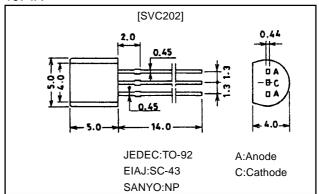
Features

• Twin type FM electronic tuning-use varactor diode which excels in large input characteristics.

Package Dimensions

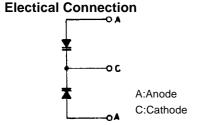
unit:mm

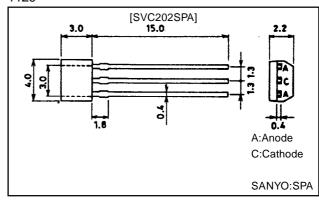
1074A



unit:mm

1129





Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	٧R		-16	V
Junction Temperature	Tj		100	°C
Storage Temperature	Tstg		-55 to +100	°C

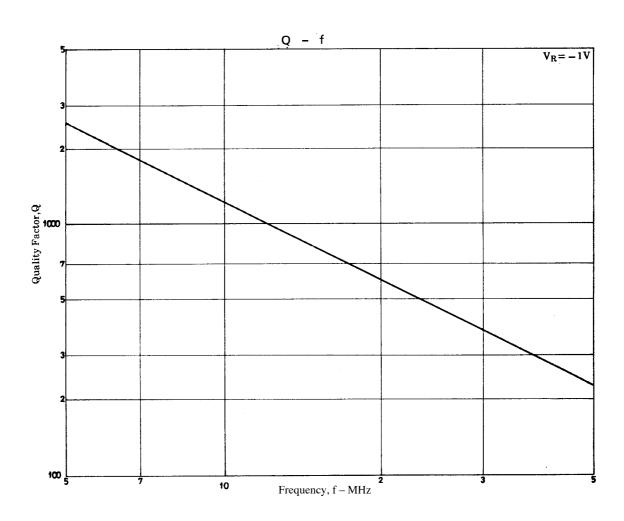
Electrical Characteristics at Ta = 25°C

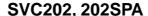
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Breakdown Voltage	V(BR)R	I _R =-10μA	-16			V
Reverse Current	IR	V _R =-9V			-50	nA
Interterminal Capacitance*	C _{1.6V}	V _R =-1.6V, f=1MHz	28.19		37.45	pF
	C _{3.5V}	V _R =-3.5V, f=1MHz	19.04		24.33	pF
	C _{5.0V}	V _R =-5.0V, f=1MHz	14.48		18.49	pF
	C _{7.5V}	V _R =-7.5V, f=1MHz	10.17		12.99	pF
Capacitance Ratio	CR	C _{1.6V} /C _{7.5V} , f=1MHz	2.2		3.7	
Series Resistance	r _s	f=50MHz, V _R =-1V			0.6	Ω
Matching Tolerance	ΔC _m	(C _{max} -C _{min})/C _{min}			0.05	

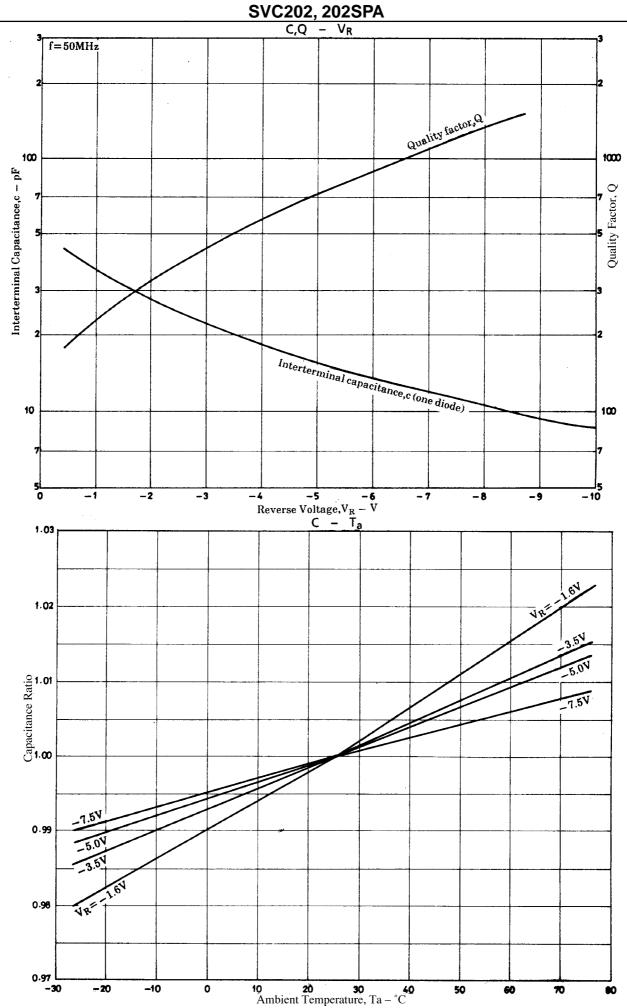
Note)*:Capacitance value of one diode

Address and Capacitance Value (one diode)

C 1.6V	C 3.5V	C 5.0V	C 7.5V		
Address Capacitance (pF)	Address Capacitance (pF)	Address Capacitance (pF)	Address Capacitance (pF)		
38 [37.45 35.67	27 [^{24.33} _{23.17}	20 [18.49 17.61	11 [^{12.99} _{12.37}		
37 [36.01	26 [23.39	19 [17.78	10 [12.50		
34.30	22.28	16.93	11.90		
36 [34.63	25 [22.49	18 [17.09	9 [12.01		
32.98	21.42	16.28	11.44		
35 [33.30	24 [21.63	.17 [16.43	8 [11.54		
31.71	20.60	15.65	10.99		
34 [32.02	23 [20.80	16 [15.81	7 [\frac{11.11}{10.58}		
30.50	19.81	15.05			
33 [30.79	22 [20.00	15 [15.20	6 [10.68		
29.32	19.04	14.48	10.17		
32 [29.60 28.19					
	Address Capacitance (pF) 38	Address Capacitance (pF) 38	Address Capacitance (pF) Address Capacitance (pF) Address Capacitance (pF) Address Capacitance (pF) 38 [37.45		







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